2524-N • 2525-N

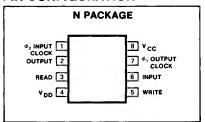
DESCRIPTION

The 2525 1024-bit recirculating dynamic shift register consists of enhancement mode p-channel MOS devices integrated on a single monolithic chip. Internal recirculation logic plus write and read controls are included on the chip.

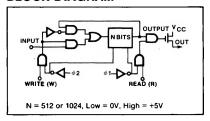
TRUTH TABLE

WRITE	READ	READ FUNCTION						
0		Recirculate, Output is '0'						
0	1	Recirculate, Output is data						
1	0	Write mode, Output is '0'						
1	1	Read mode, Output is data						

PIN CONFIGURATION



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS1

	PARAMETER	RATING	UNIT
	Temperature range ²		°C
T_A	Operating	0 to 70	
TSTG	Storage	-65 to 150	
PD	Power dissipation at T _A > 70°C ²	535	mW
	Data and clock input voltages and supply voltages with respect to V _{CC}	0.3 to -20	V

DC ELECTRICAL CHARACTERISTICS $T_A = 0$ °C to 70°C, $V_{CC} = 5V \pm 5\%$, $V_{DD} = -5V \pm 5\%$ unless otherwise specified.

PARAMETER		TEST COMPLETIONS	2524			2525			UNIT
		TEST CONDITIONS		Тур	Max	Min	Тур	Max	UNII
VIL VIH VILC VIHC	Input voltage ³ Low High Clock low Clock high	-	-5.0 3.4 -12.0 4.0		0.6 5.3 -10.0 5.3	-5.0 3.4 -12.0 4.0		0.6 5.3 -10.0 5.3	V
Vol Voh1 Voh2	Output voltage Low, driving 1 TTL load High, driving 1 TTL load High, driving MOS	$R_L = 3.0 \text{K}$, 1 TTL load ($I_L = 1.6 \text{mA}$) ⁴ $R_L = 3.0 \text{K}$, 1 TTL load ($I_L = 100 \mu \text{A}$) $R_L = 5.6 \text{K}$, $C_L = 10 \text{pF}$	2.4 3.6	-1.0 3.5 4.0		2.4 3.6	-1.0 3.5 4.0		V
l _{LI}	Input load current	V _{IN} = -5.5V, T _A = 25°C		10	500		10	500	nA
ILO ILC	Leakage current Output Clock	$T_A = 25^{\circ}C$ $V_{\phi 2} = V_{\phi 1} = -12V, V_{DD} = -5, V_{OUT} = -5.5V$ $V_{ILC} = -12V$		10 10	1000 1000		10 10	1000 1000	nA
IDD	Supply current	Continuous operation, ϕ pW = 150ns, f = 1MHz, V_{ILC} = -12V, T_A = 25°C, V_{DD} = -5.5V		15	35		25	35	mA
Cin Cout Cø	Capacitance Input Output Clock	1MHz, V _{AC} = 25mV p-p V _I = V _{CC} V _O = V _{CC} V = V _{CC}			5 5 80			5 5 160	pF

2524-N • 2525-N

AC ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C$, $V_{CC} = 5V \pm 5\%$, $V_{DD} = -5V \pm 5\%$, $V_{ILC} = -11V$,

Input rise and fall times = 10ns, Output load = 1 TTL gate

PARAMETER			FROM		LIMITS			
		ТО		TEST CONDITIONS	Min	Тур	Max	UNIT
Freq.	Clock data rep rate5			W = R = V _{CC}	.0005	5	3 -	MHz
t∳PW	Clock pulse width	j			135	85		ns
tøD	Clock pulse delay				10			ns
t _R ,t _F	Clock pulse transition				10		1000	ns
	Setup and hold time							ns
tow	Setup time	Clock	Data in		70			
tDH	Hold time	Data in	Clock		20			
t _{A+}	Delay time	Data out	Clock				100	ns
t _{R-} ,tw-	Clock to read or write timing				0	ľ	Ϊ '	ns
t _{R-} ,t _{W+}	Clock to read or write timing				0			ns

NOTES

- 1. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied.
- 2. For operating at elevated temperatures the device must be derated based on a +150°C maximum junction temperature and a thermal resistance of 150°C/W junction to ambient.
- 3. Guaranteed input levels are stated for worst case conditions including a $\pm 5\%$ variation in VCC and a temperature variation of 0°C to +70°C. Actual input requirements with respect to V_{CC} are V_{IH} = V_{CC}-1.85V and VIL = VCC - 4.15V.
- 4. Vol is a function of the input characteristics of the driven TTL/DTL gate IoI and Volamp and the value of the pull-down resistor (RL).
- 5. See Minimum Operating Frequency graph for low limits on data rep. rate.
- 6. All inputs are protected against static charge.
- 7. All voltage measurements are referenced to ground.
- 8. Manufacturer reserving the right to make design and process changes and improvements.
- 9. Typical values are at +25°C and typical supply voltages.
- 10. Parameters are valid over operating temperature range unless otherwise specified.

TIMING DIAGRAM

